

Please amend the following claim:

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21. (Amended) A method for fabricating a semiconductor apparatus, comprising:
fabricating a semiconductor substrate which comprises a semiconductor integrated circuit, and an electrode, which is composed of a base member of insulating material formed on the semiconductor integrated circuit and a conductive layer formed on the surface of the base member;
placing the semiconductor substrate to face a connection substrate;
connecting the electrode to the connection substrate; and
supplying a seal member in the space between the semiconductor substrate and the connection substrate.

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Please add the following claims:

--22. A method according to claim 21, wherein
the semiconductor substrate is placed to face the connection substrate according to a face down technique.

23. A method according to claim 21, wherein
the base member and the seal member are made of the same material.--